

FIG.1

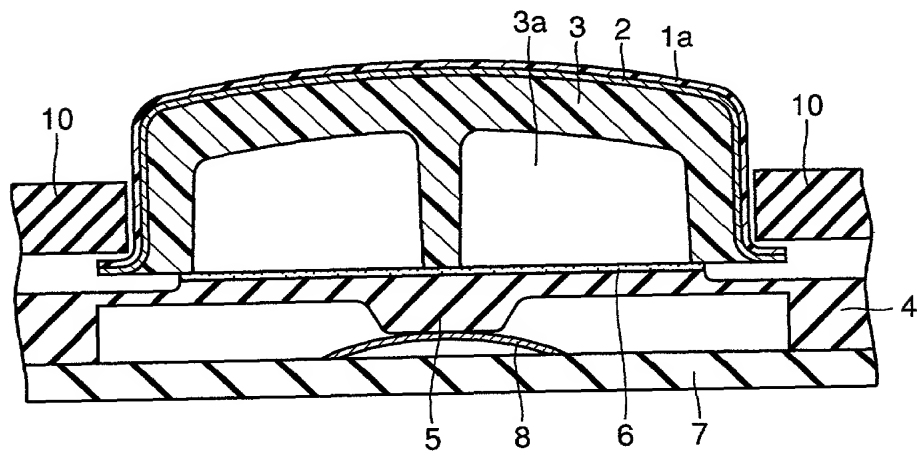


FIG.2

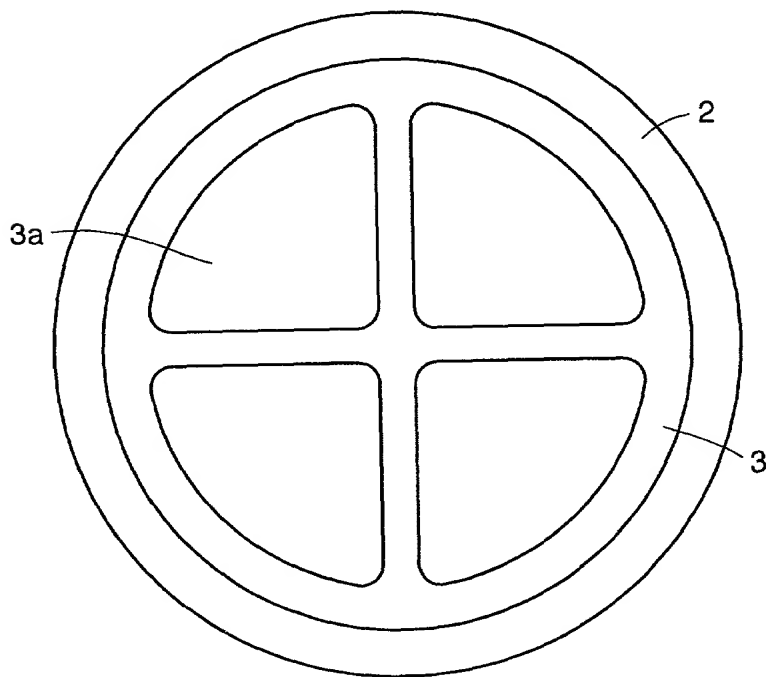


FIG.3

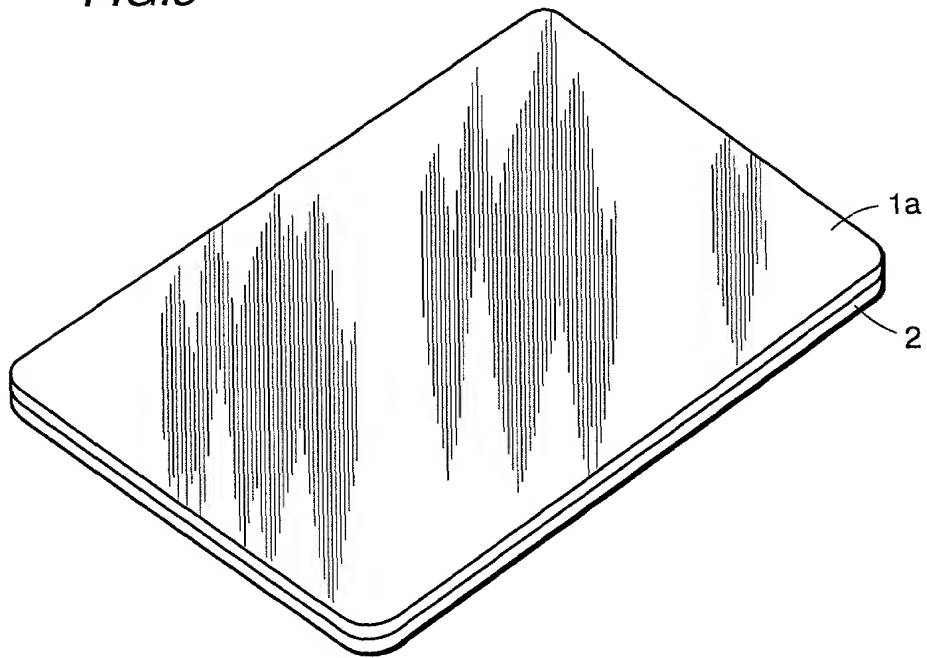


FIG.4

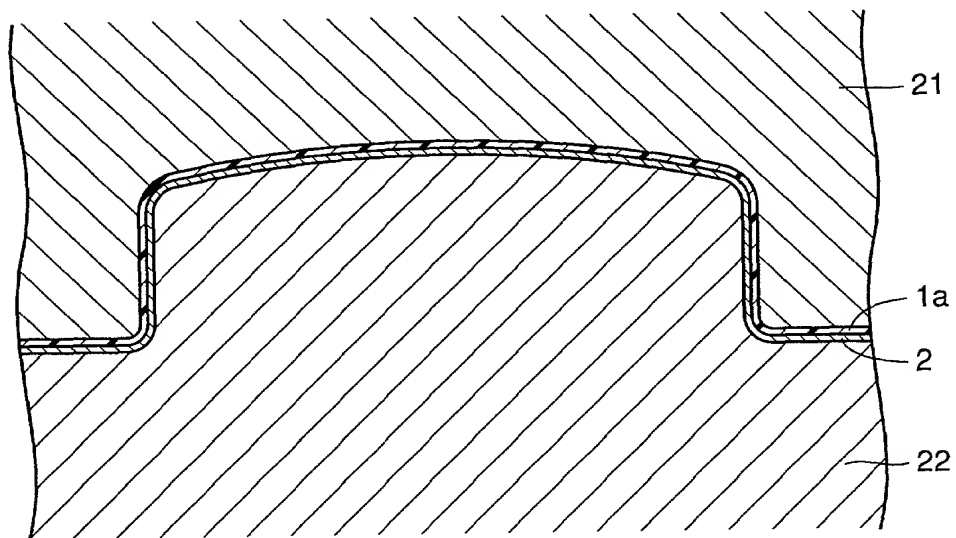


FIG.5

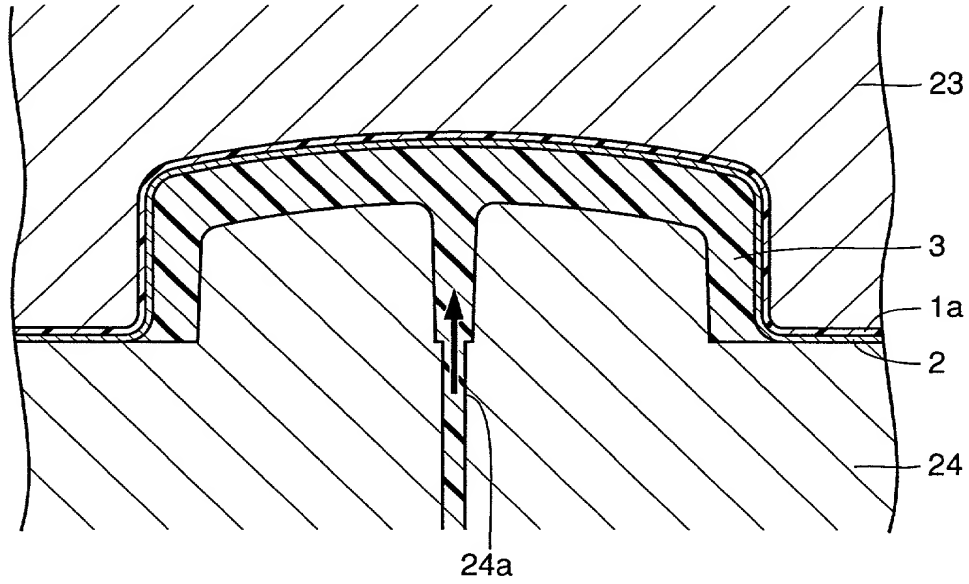
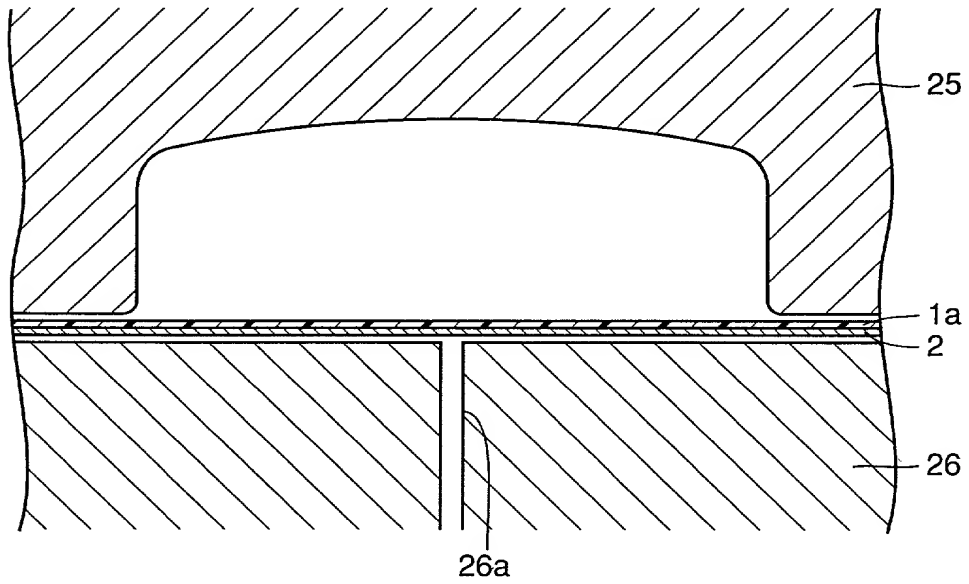


FIG.6



This diagram shows a cross-section of a device. A central cavity, labeled 3, is filled with a material indicated by diagonal hatching. This cavity is bounded by a top surface 1a and side walls 2. The entire assembly is housed within a larger structure 25. A vertical probe or needle, labeled 26a, is shown entering the cavity from the bottom. Arrows within the cavity point towards the probe, suggesting a flow or interaction. The bottom boundary of the device is labeled 26.

This cross-sectional view shows a semiconductor device with a central gap. The device consists of a substrate (4) with a central region (5) and side regions (6). A layer (7) is formed on the substrate, and a layer (8) is formed on the central region (5). A layer (3) is formed on the side regions (6), and a layer (3a) is formed on the central region (5). A layer (11) is formed on the side regions (6), and a layer (2) is formed on the central region (5). A layer (1a) is formed on the side regions (6), and a layer (10) is formed on the central region (5).

FIG.9

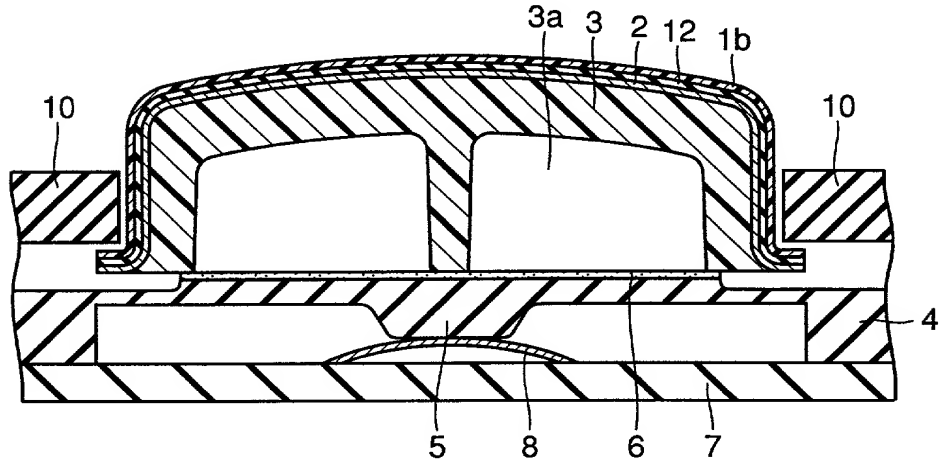


FIG.10

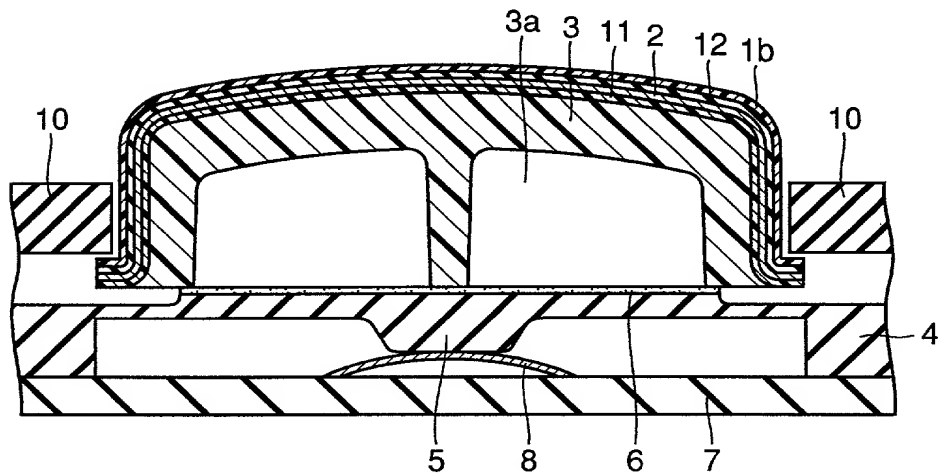


FIG.11

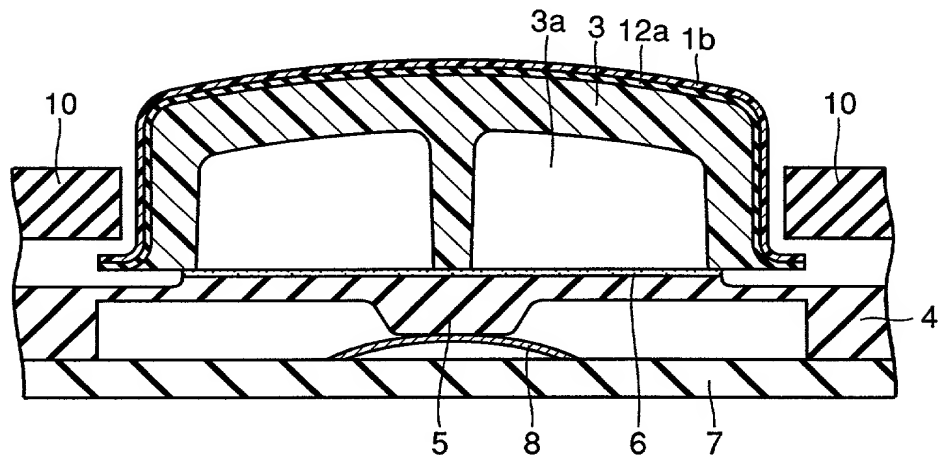


FIG.12

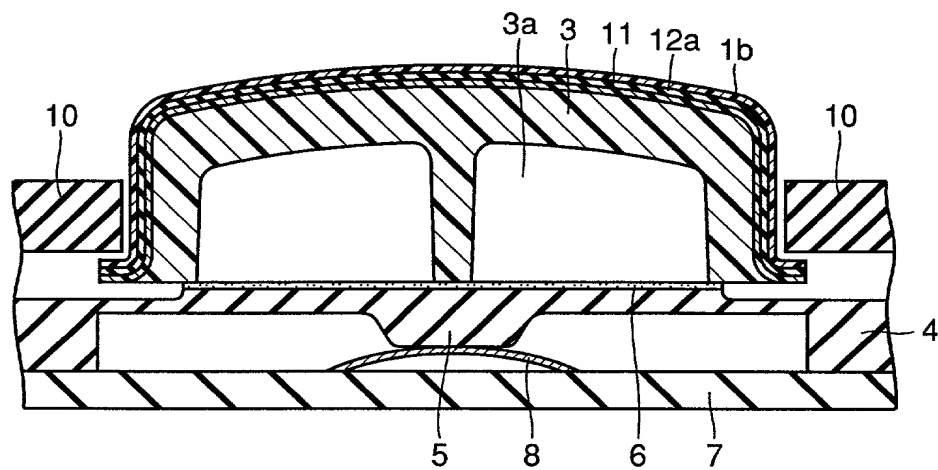


FIG. 13

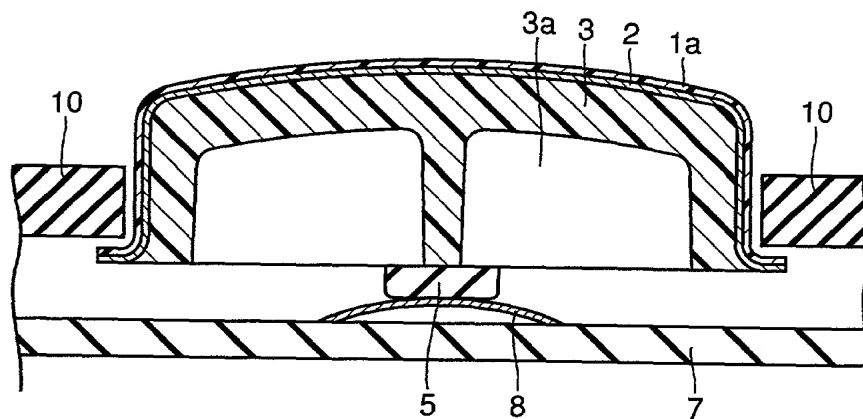


FIG. 14

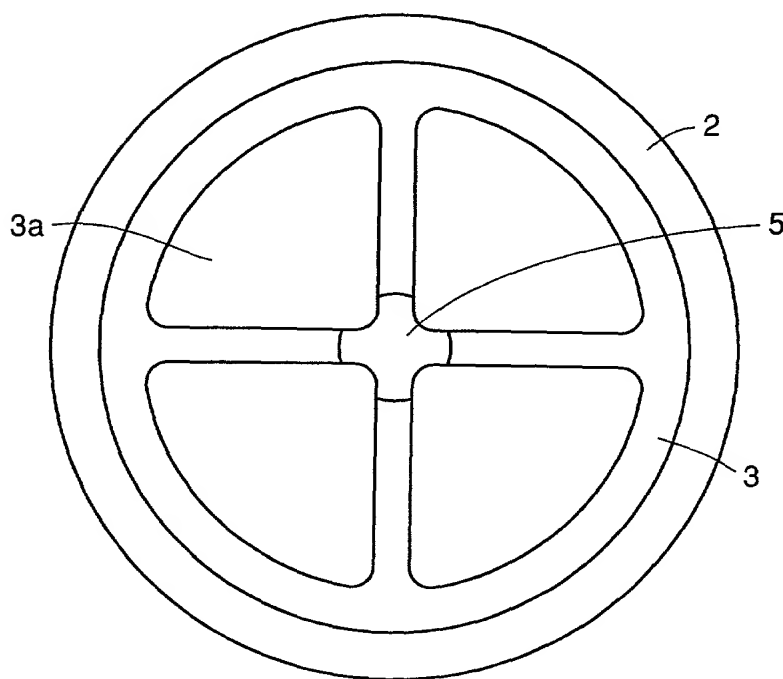


FIG.15 PRIOR ART

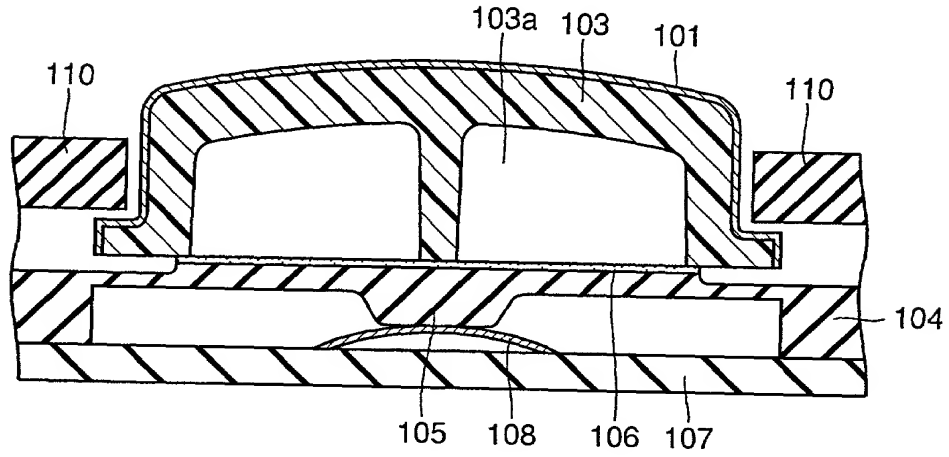


FIG. 15 PRIOR ART